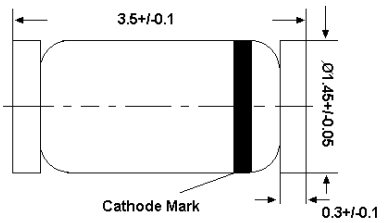
BAS81

Silicon Schottky Barrier Diodes

for general purpose applications

LL-34



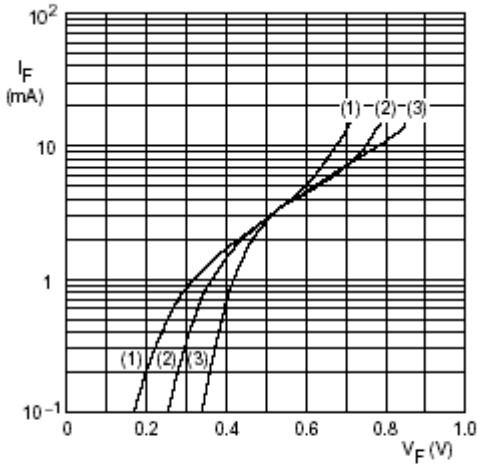
Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RRM}	40	V
Continuous Forward Current	I_F	30	mA
Repetitive Peak Forward Current $t_p \leqq 1$ s, $\delta \leqq 0.5$	I_{FRM}	150	mA
Repetitive Peak Forward Current $t_p = 1$ s	I_{FSM}	500	mA
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	320	K/W
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 65 to + 150	°C

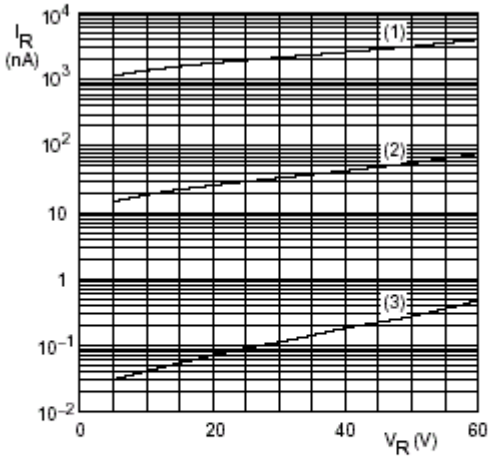
Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 0.1 mA at I_F = 1 mA at I_F = 15 mA	V_F	 0.33 0.41 1	V
Reverse Current at V_R = 40	I_R	200	nA
Total Capacitance at V_R = 2 V, f = 1 MHz	C_{tot}	1.6	pF



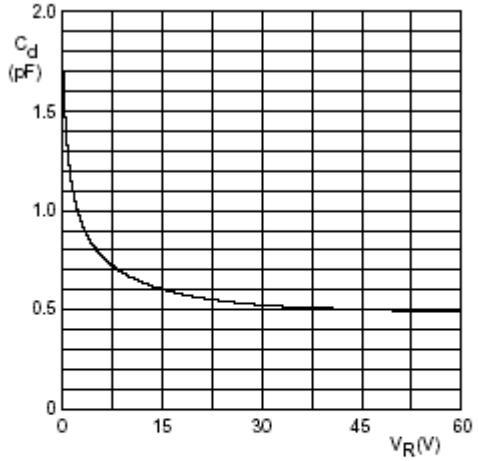
(1) T_{amb} = 85 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −40 °C.

Forward current as a function of forward voltage; typical values.



(1) T_{amb} = 85 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −40 °C.

Reverse current as a function of reverse voltage; typical values.



f = 1 MHz.

Diode capacitance as a function of reverse voltage; typical values.